GSDSRB521N1-30F

Schottky Diode

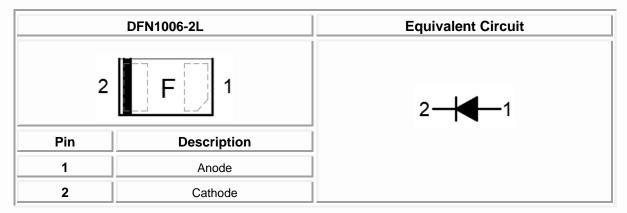
Product Description

Schottky Barrier Diode 150mW / 30V

Features

- Low Forward Voltage
- RoHS compliant
- UL-94 V-0 / Green EMC
- Matte Tin Lead Finish (Pb-Free)

Packages & Pin Assignments



Ordering and Marking Information

Part Number	Package	Package Part Marking	
GSDSRB521N1-30F	DFN1006-2L	F	10000 PCS
Product Code:	- Package Code:	- Voltag	ge Code:
GSDSRB521	N1 is DFN1006-2L		
F is RoHS Compliant a			
Halogen Free			
Halogen Free	Marking Infor	nation	



Absolute Maximum Ratings (T_A=25°C unless otherwise noted)

Symbol	Parameter	Rating	Unit
V _R	Reverse Voltage	30	V
l _F	Average Forward Current	200	mA
IFSM	Non-Repetitive Peak Forward Current *	500	mA
PD	Power Dissipation T _A =25°C	150	mW
TJ	Junction Temperature Range	125	°C
T _{STG}	Storage Temperature Range	-55 to +125	°C

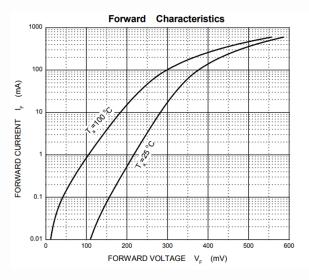
^{* 8.3}ms Single Half Sine-Wave

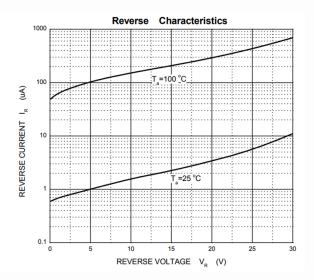
Electrical Characteristics (T_A=25°C unless otherwise specified)

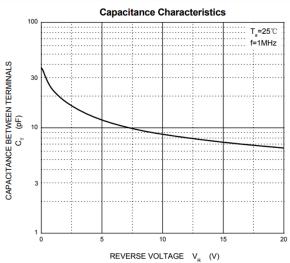
Symbol	Description	Conditions	Min	Max	Unit
V_R	Reverse Voltage	I _R =0.1mA	30	-	V
I _R	Reverse Current	V _R =10V	-	30	μΑ
V	Famurand Valtana	I _F =10mA	-	0.35	V
V _F	Forward Voltage	I _F =200mA	-	0.50	V

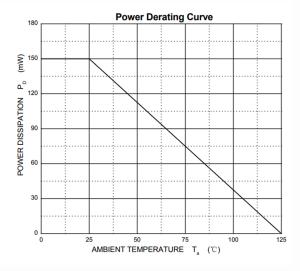


Performance Characteristics (T_A=25°C unless otherwise specified)





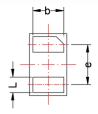




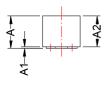


DFN1006-2L

Package Dimension

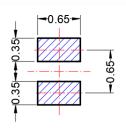


BACKSIDE VIEW





Recommended Land Pattern



(Unit: mm)

	Dimensions			
Symbol	Millimeters		Inches	
Symbol	Min	Max	Min	Max
Α	0.45	0.60	0.018	0.024
A1	0.00	0.05	0.000	0.002
A2	0.40	0.60	0.016	0.024
b	0.45	0.55	0.018	0.022
D	0.55	0.65	0.022	0.026
E1	0.95	1.05	0.037	0.041
e1	0.65 BSC		0.02	26 BSC
L	0.20	0.30	0.008	0.012

NOTE:

DIMENSION D DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.



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